

<b>SANYO</b>	No.3557A	<b>2SK1419</b>
		N-Channel MOS Silicon FET Very High-Speed Switching Applications

**Features**

- Low ON resistance.
- Very high-speed switching.
- Converters.
- Micaless package facilitating mounting.

**Absolute Maximum Ratings at Ta = 25°C**

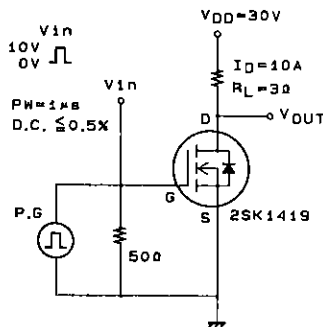
			unit
Drain to Source Voltage	V <sub>DSS</sub>	60	V
Gate to Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current(DC)	I <sub>D</sub>	15	A
Drain Current(Pulse)	I <sub>DP</sub>	PW ≤ 10μs, duty cycle ≤ 1%	A
Allowable Power Dissipation	P <sub>D</sub>	T <sub>c</sub> = 25°C	25 W
			2.0 W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 1mA, V <sub>GS</sub> = 0	60			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0			100	μA
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0			±100	nA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	1.5		2.5	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 10A	6.0	10		S
Static Drain to Source on State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> = 10A, V <sub>GS</sub> = 10V		60	80	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 20V, f = 1MHz		750		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 20V, f = 1MHz		350		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 20V, f = 1MHz		90		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	I <sub>D</sub> = 10A, V <sub>GS</sub> = 10V V <sub>DD</sub> = 30V, R <sub>GS</sub> = 50Ω		12		ns
Rise Time	t <sub>r</sub>		43		ns	
Turn-OFF Delay Time	t <sub>d(off)</sub>		90		ns	
Fall Time	t <sub>f</sub>		60		ns	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 15A, V <sub>GS</sub> = 0			1.8	V

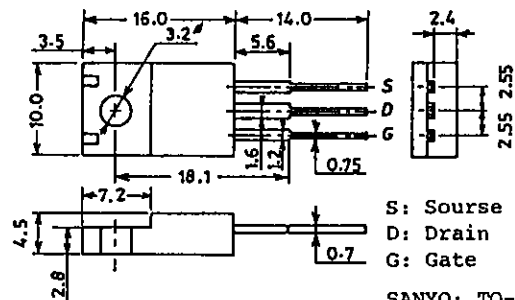
(Note) Be careful in handling the 2SK1419 because it has no protection diode between gate and source.

**Switching Time Test Circuit**



**Package Dimensions 2063**

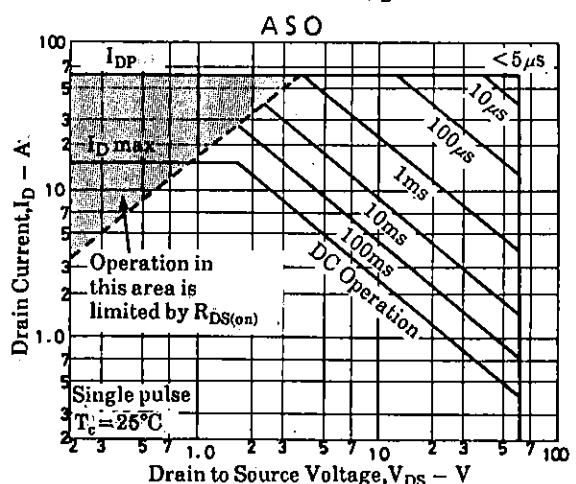
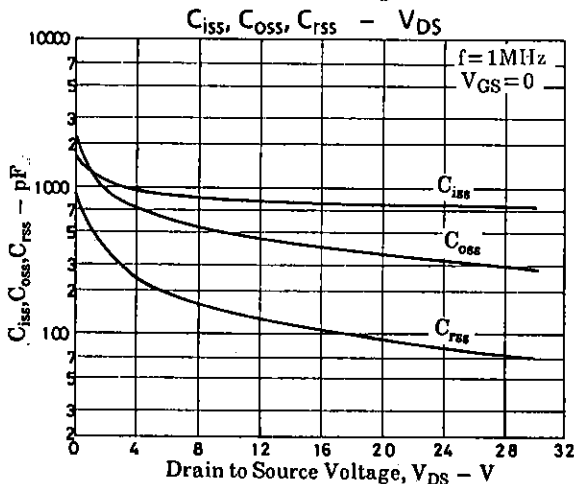
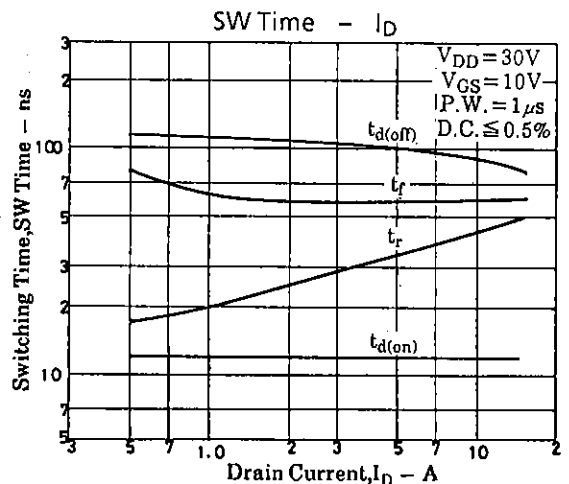
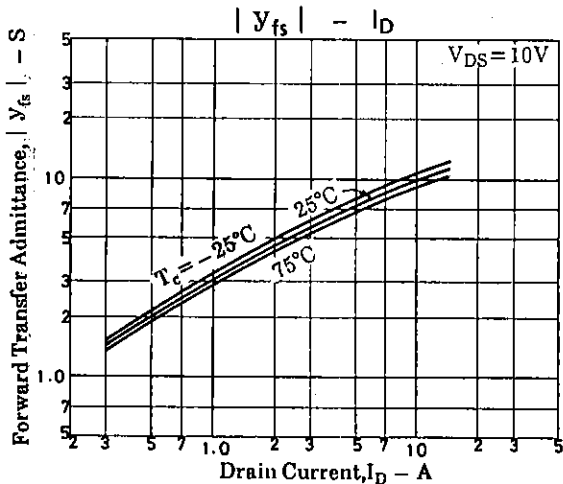
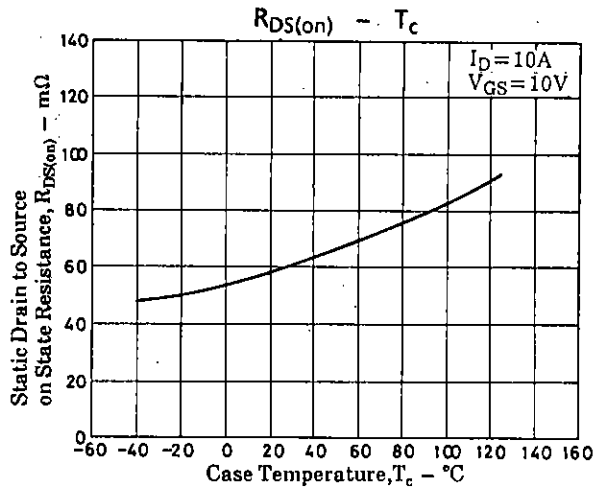
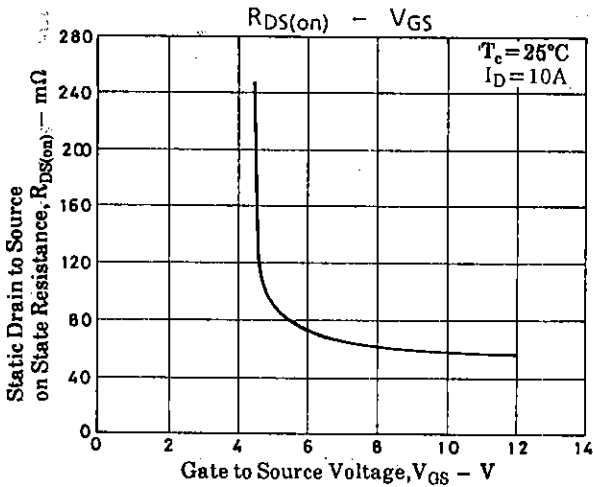
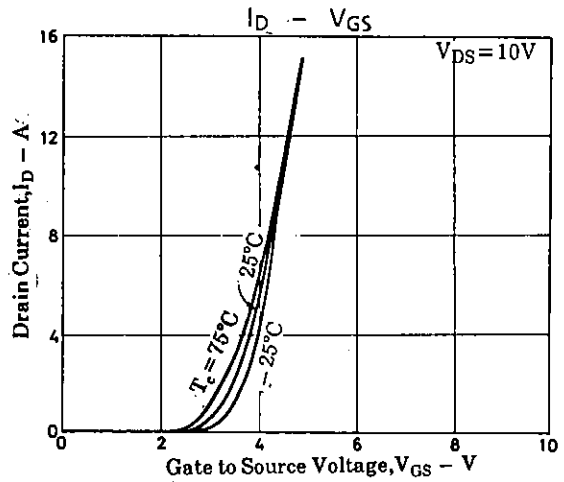
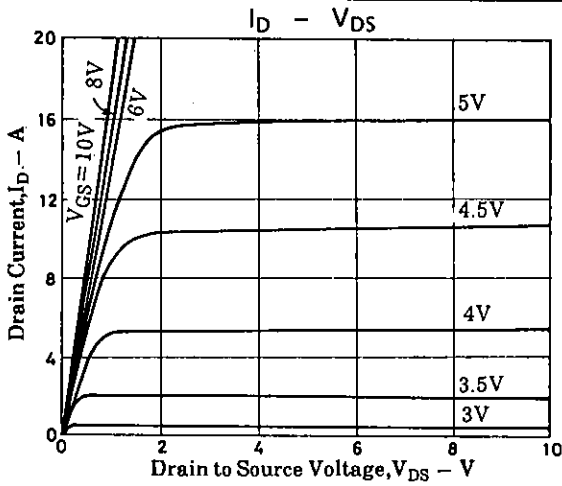
(unit: mm)

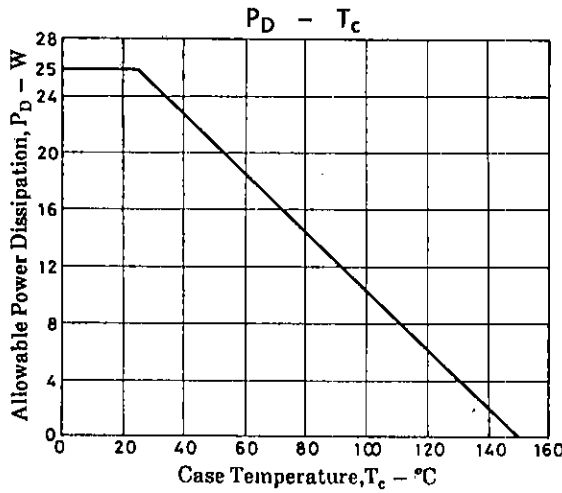
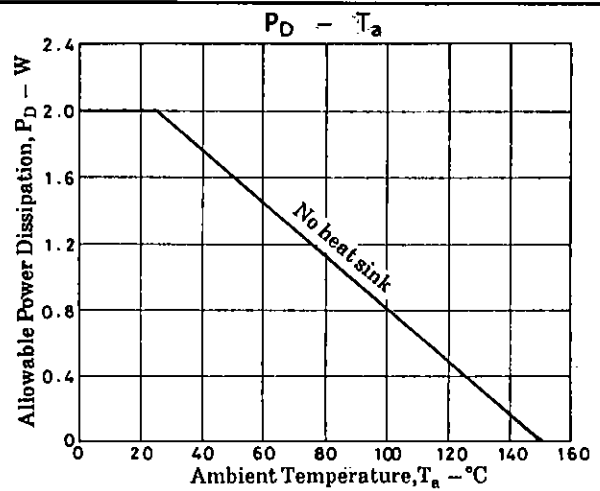
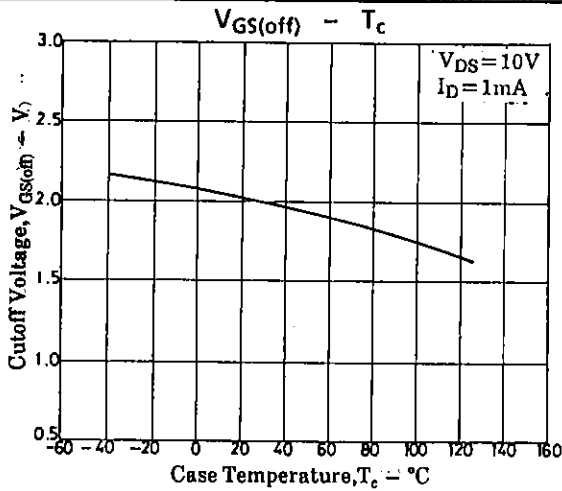


S: Source  
D: Drain  
G: Gate

SANYO: TO-220ML

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